JAN/JANTX/JANTXV 4N22, 4N23, 4N24 [A]



Features:

- TO-78 hermetically sealed package
- High current transfer ratio
- 1 kV electrical isolation
- Base contact provided for conventional transistor biasing
- JAN, JANTX and JANTXV devices processed to MIL-PRF-19500
- Patent No. 4124860



Description:

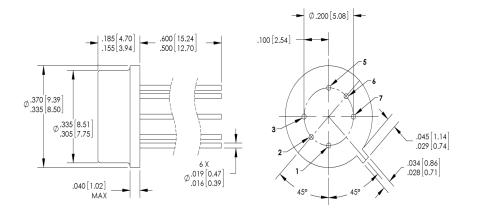
Each isolator in this series consists of an infrared emitting diode and a NPN silicon phototransistor, which are mounted in a hermetically sealed TO-78 package. Devices are designed for military and/or harsh environments. The suffix letter "A" denotes the collector is electrically isolated from the case.

The JAN / JANTX / JANTXV 4N22, 4N22A, 4N23A, 4N23A, 4N24, and 4N24A devices are processed to MIL-PRF-19500/486. This series of 4N products are JEDEC registered, DSCC qualified.

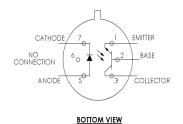
Please contact your local representative for more information.

Applications:

- High-voltage isolation between input and output
- Electrical isolation in dirty environments
- Industrial equipment
- Medical equipment
- Office equipment



DIMENSIONS ARE IN INCHES [MIM]



Pin #	Function	Pin #	Function
3	Collector	5	Anode
2	Base	6	Open
1	Emitter	7	Cathode

General Note

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Electrical Specifications

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Storage Temperature Range	-65°C to 150°C		
Operating Temperature Range	-55°C to +125°C		
Input-to-Output Isolation Voltage	± 1.00 kVDC ⁽¹⁾		
Lead Soldering Temperature [1/16 inch (1.6mm) from case for 5 seconds with soldering iron]	260°C ⁽²⁾		
ESD Class	1C		
Input Diode			
Forward DC Current (65°C or below)	40 mA		
Reverse Voltage	2 V		
Peak Forward Current (1 μs pulse width, 300 pps)	1 A		
Power Dissipation	60 mW ⁽³⁾		
Output Sensor:			
Continuous Collector Current	50 mA		
Collector-Emitter Voltage	40 V		
Collector-Base Voltage	45 V		
Emitter-Base Voltage	4 V		
Power Dissipation	300 mW ⁽⁴⁾		

Notes:

- 1. Measured with input leads shorted together and output leads shorted together.
- RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- 3. Derate linearly 1.0 mW/° C above 65° C.
- 4. Derate linearly 3.0 mW/° C above 25° C.

Ordering Information						
Part Number	Isolation I _F (mA) Voltage (kV) Typ / Max		V _{CE} (Volts) Max	Processing MIL-PRF- 195000		
JAN4N22 or JAN4N22A						
JANTX4N22 or JANTX4N22A						
JANTXV4N22 or JANTXV4N22A						
JAN4N23 or JAN4N23A						
JANTX4N23 or JANTX4N23A	1	10 / 40	40	486		
JANTXV4N23 or JANTXV4N23A						
JAN4N24 or JAN4N24A						
JANTX4N24 or JANTX4N24A						
JANTXV4N24 or JANTXV4N24A						





Electrical Characteristics (T_A = 25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS		
Input Diode								
V_{F}	Forward Voltage	0.80 1.00 0.70	- - -	1.50 1.70 1.30	V	$I_F = 10.0 \text{ mA}$ $I_F = 10.0 \text{ mA}, T_A = -55^{\circ} C^{(1)}$ $I_F = 10.0 \text{ mA}, T_A = +100^{\circ} C^{(1)}$		
I _R	Reverse Current	-	-	100	μΑ	V _R = 2.0 V		
Output Pl	hototransistor							
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	40	-	-	V	I _C = 1.0 mA, I _B = 0, I _F = 0		
V _{(BR)CBO}	Collector-Base Breakdown Voltage	45	-	-	V	I _C = 100 μA, I _B = 0, I _F = 0		
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	7	-	-	V	I _E = 100 μA, I _C = 0, I _F = 0		
I _{C(OFF)}	Collector-Emitter Dark Current	-	-	100 100	nA μA	$V_{CE} = 20 \text{ V}, I_B = 0, I_F = 0$ $V_{CE} = 20 \text{ V}, I_B = 0, I_F = 0, T_A = 100^{\circ}\text{C}$		
I _{CB(OFF)}	Collector-Base Dark Current	-	-	100	nA	$V_{CB} = 20 \text{ V}, I_E = 0, I_F = 0$		
Coupled								
	On-State Collector Current JAN / JANTX / JANTXV 4N22 [A]	0.15 2.50 1.00 1.00	- - -	- - -		$I_F = 2.0 \text{ mA}, V_{CE} = 5 \text{ V}, I_B = 0$ $I_F = 10.0 \text{ mA}, V_{CE} = 5 \text{ V}, I_B = 0$ $I_F = 10.0 \text{ mA}, V_{CE} = 5 \text{ V}, I_B = 0, T_A = -55^{\circ} \text{ C}^{(1)}$		
I _{C(ON)}	JAN / JANTX / JANTXV 4N23 [A]	0.20 6.00 2.50 2.50	- - -	- - -	mA	$I_F = 2.0 \text{ mA}, V_{CE} = 5 \text{ V}, I_B = 0$ $I_F = 10.0 \text{ mA}, V_{CE} = 5 \text{ V}, I_B = 0$ $I_F = 10.0 \text{ mA}, V_{CE} = 5 \text{ V}, I_B = 0, T_A = -55^{\circ} \text{ C}^{(1)}$		
	JAN / JANTX / JANTXV 4N24 [A]	0.40 10.0 4.00 4.00	- - -	- - -		$I_F = 2.0 \text{ mA}, V_{CE} = 5 \text{ V}, I_B = 0$ $I_F = 10.0 \text{ mA}, V_{CE} = 5 \text{ V}, I_B = 0$ $I_F = 10.0 \text{ mA}, V_{CE} = 5 \text{ V}, I_B = 0, T_A = -55^{\circ} \text{ C}^{(1)}$		
V _{CE(SAT)}	Collector-Emitter Saturation Voltage JAN / JANTX / JANTXV 4N22 [A] JAN / JANTX / JANTXV 4N23 [A] JAN / JANTX / JANTXV 4N24 [A]		- - -	0.30 0.30 0.30	V	I _F = 20 mA , I _C = 2.5 mA, I _B = 0 I _F = 20 mA , I _C = 5.0 mA, I _B = 0 I _F = 20 mA , I _C = 10.0 mA, I _B = 0		
H_FE	DC Current Gain	100	-	-	V	$V_{CE} = 5.0 \text{ V}$, $I_C = 10.0 \text{ mA}$, $I_F = 0 \text{ mA}$		
R _{IO}	Resistance (Input-to-Output)	10 ¹¹	-	-	Ω	$V_{10} = \pm 1.0 \text{ VDC}^{(3)}$		
		1						

Notes:

 C_{IO}

 T_R, T_F

1. Guaranteed but not tested.

Capacitance (Input-to-Output)

Output Rise and Fall Time

- 2. Sample tested, LTPD = 10.
- 3. Measured with input leads shorted together and output leads shorted together.

General Note

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 $V_{I-O} = 0 V$, $f = 1.0 MHz^{(3)}$

 V_{CC} = 10.0 V , I_F = 10.0 mA, R_L = 100 Ω

pF

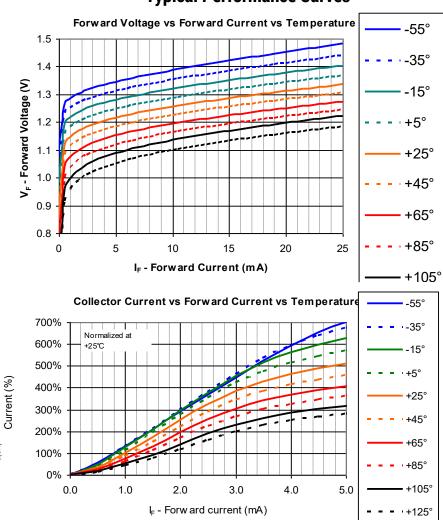
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20.0



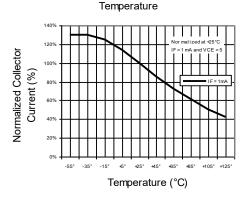


Typical Performance Curves

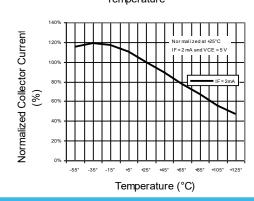


Normalized Collector Current Vs

l_{C(ON)} - Normalized Collector



Normalized Collector Current Vs Temperature



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